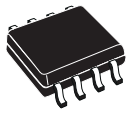
STS1HNK60

N-CHANNEL 600V - 8Ω - 0.3A SO-8
SuperMESH™Power MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D	Pw
STS1HNK60	600 V	< 8.5 Ω	0.3 A	2 W

- TYPICAL $R_{DS}(on)$ = 8 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- NEW HIGH VOLTAGE BENCHMARK

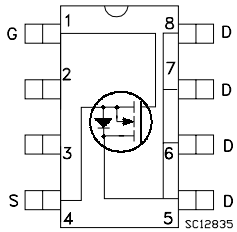


SO-8

DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

INTERNAL SCHEMATIC DIAGRAM



APPLICATIONS

- SWITCH MODE LOW POWER SUPPLIES (SMPS)
- LOW POWER, LOW COST CFL (COMPACT FLUORESCENT LAMPS)
- LOW POWER BATTERY CHARGERS

Obsolete Product(s) - Obsolete Product(s)

ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STS1HNK60	S1HNK60	SO-8	TAPE & REEL

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	600	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	600	V
V_{GS}	Gate- source Voltage	± 30	V
I_D	Drain Current (continuous) at T_C = 25°C	0.3	A
I_D	Drain Current (continuous) at T_C = 100°C	0.19	A
I_{DM} (•)	Drain Current (pulsed)	1.2	A
P_{TOT}	Total Dissipation at T_C = 25°C	2	W
	Derating Factor	0.016	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	3	V/ns
T_j T_{stg}	Operating Junction Temperature Storage Temperature	-65 to 150	°C

(•) Pulse width limited by safe operating area
(1) I_{SD} ≤0.3A, di/dt ≤100A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_j ≤ T_{JMAX}.

THERMAL DATA

Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_{CASE} =25°C UNLESS OTHERWISE SPECIFIED)

ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 1 mA, V_{GS} = 0	600			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating, T_C = 125 °C			1 50	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 30 V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA	2.25	3	3.7	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V, I_D = 0.5 A		8	8.5	Ω

Obsolete Product(s) - Obsolete Product(s)

ELECTRICAL CHARACTERISTICS (CONTINUED)

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, $I_D = 0.5$ A		1		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25V$, f = 1 MHz, $V_{GS} = 0$		156 23.5 3.8		pF pF pF

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 300$ V, $I_D = 0.5$ A $R_G = 4.7\Omega$ $V_{GS} = 10$ V (Resistive Load see, Figure 3)		6.5 5		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 480$ V, $I_D = 1$ A, $V_{GS} = 10V$, $R_G = 4.7\Omega$		7 1.1 3.4	10	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 300$ V, $I_D = 0.5$ A $R_G = 4.7\Omega$ $V_{GS} = 10$ V (Resistive Load see, Figure 3)		19 25		ns ns
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 480V$, $I_D = 1.0$ A, $R_G = 4.7\Omega$, $V_{GS} = 10V$ (Inductive Load see, Figure 5)		24 25 44		ns ns ns

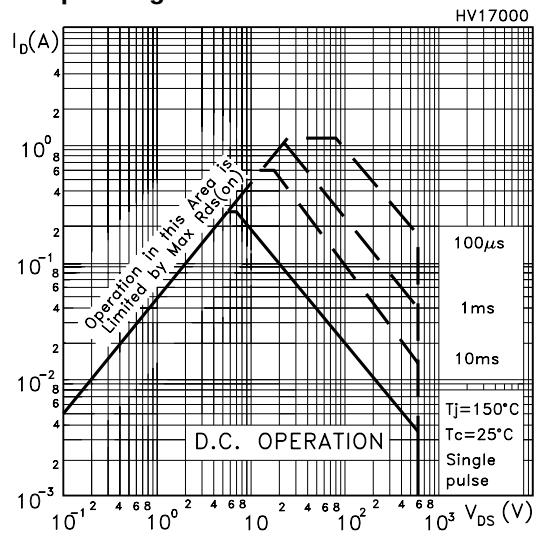
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (2)	Source-drain Current Source-drain Current (pulsed)				0.3 1.2	A A
V_{SD} (1)	Forward On Voltage	$I_{SD} = 0.3$ A, $V_{GS} = 0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 0.3$ A, di/dt = 100 A/µs $V_{DD} = 25$ V, $T_j = 150°C$ (see test circuit, Figure 5)		229 377 3.3		ns µC A

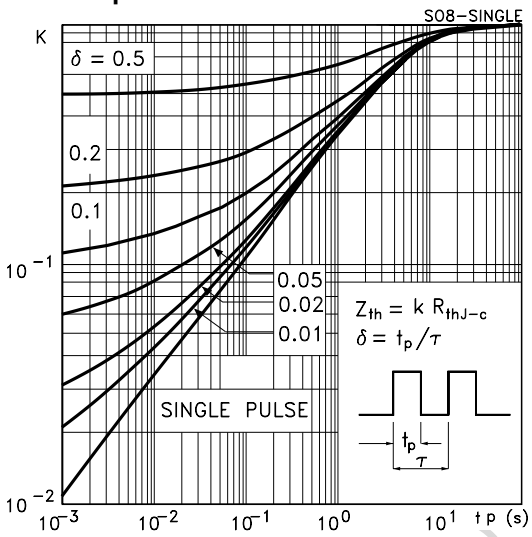
Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

Obsolete Product(s) - Obsolete Product(s)

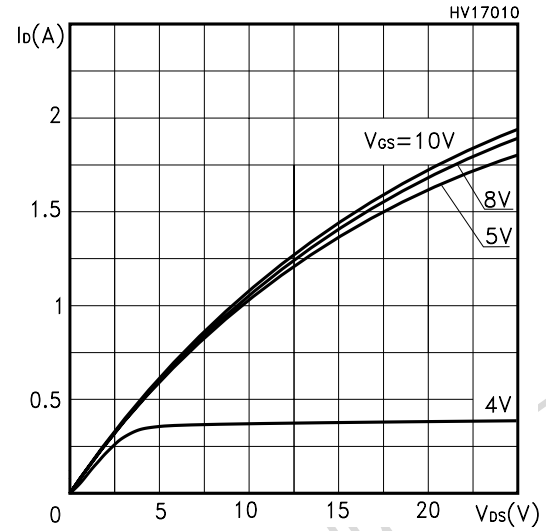
Safe Operating Area



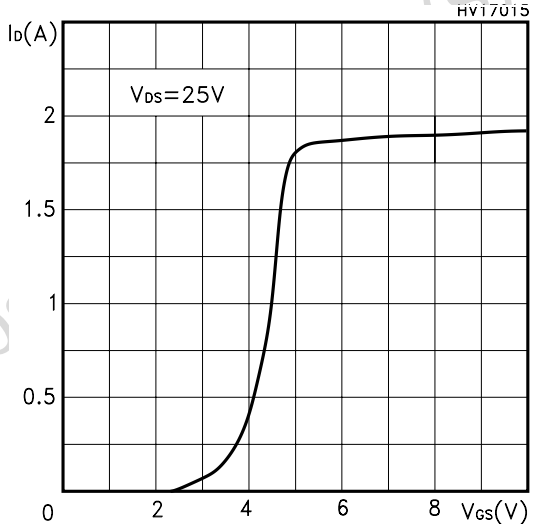
Thermal Impedance



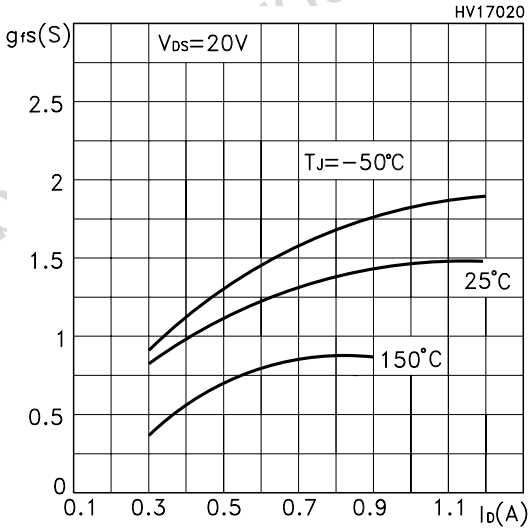
Output Characteristics



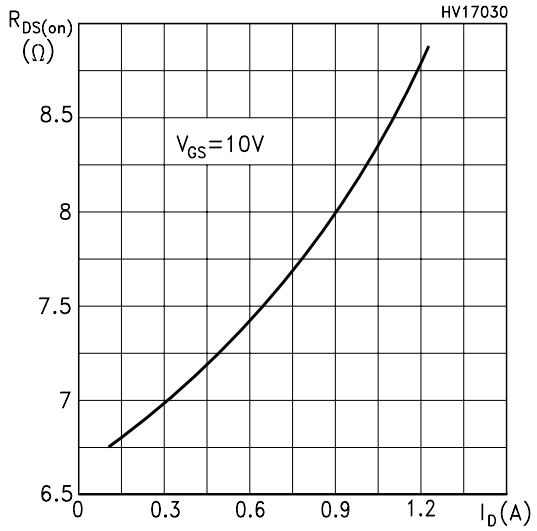
Transfer Characteristics



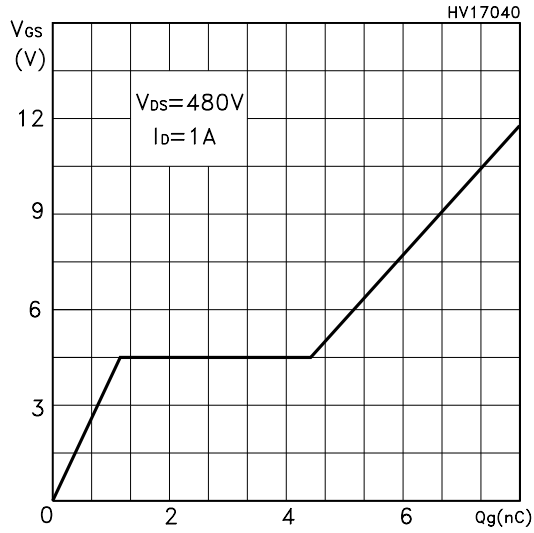
Transconductance



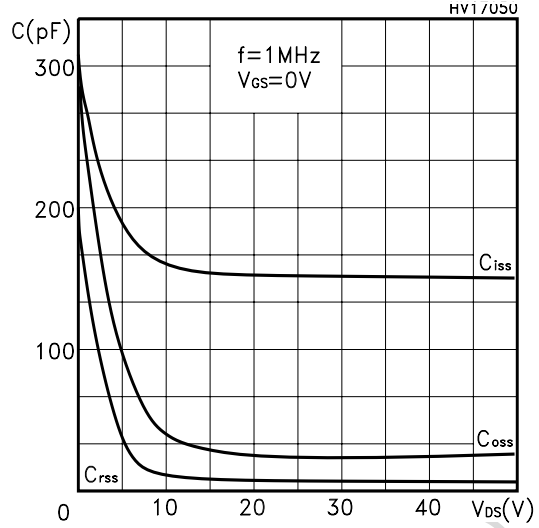
Static Drain-source On Resistance



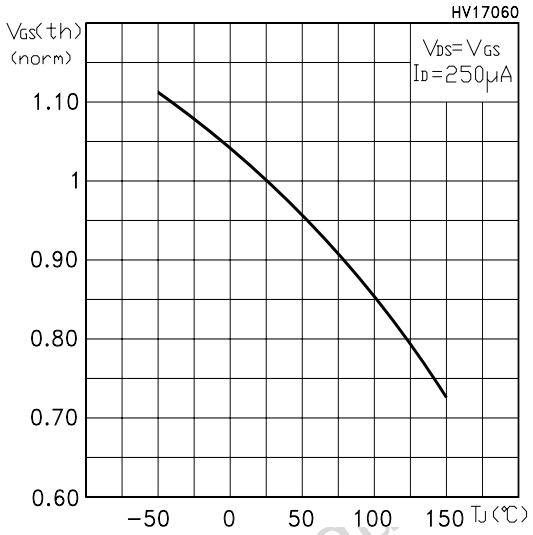
Gate Charge vs Gate-source Voltage



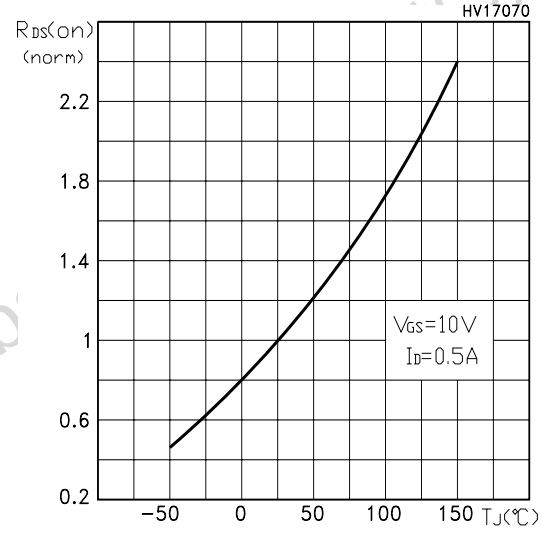
Capacitance Variations



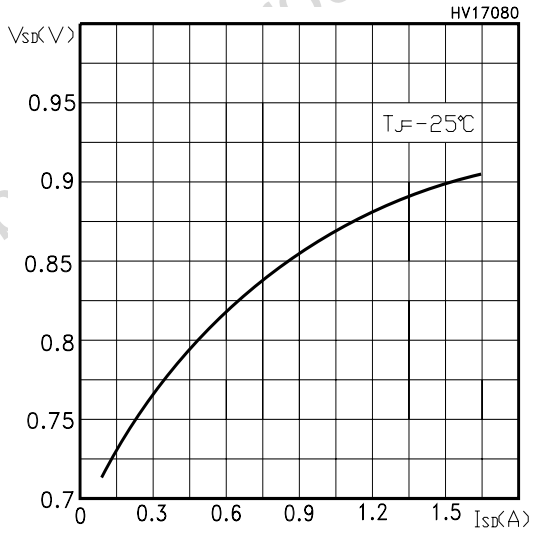
Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized BVDSS vs Temperature

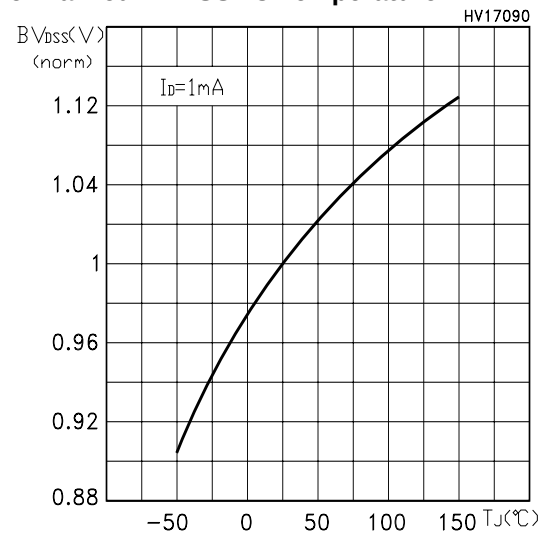


Fig. 1: Unclamped Inductive Load Test Circuit

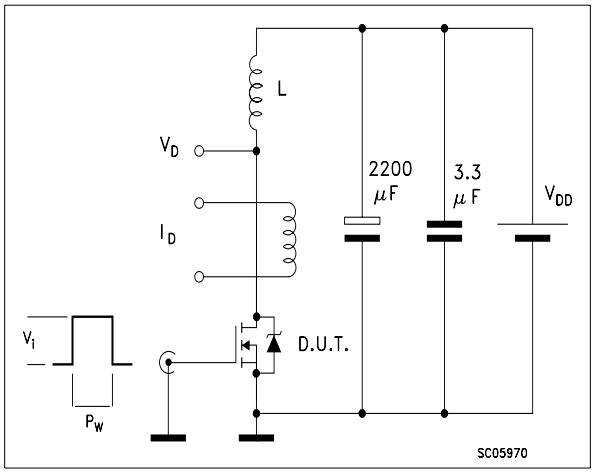


Fig. 2: Unclamped Inductive Waveform

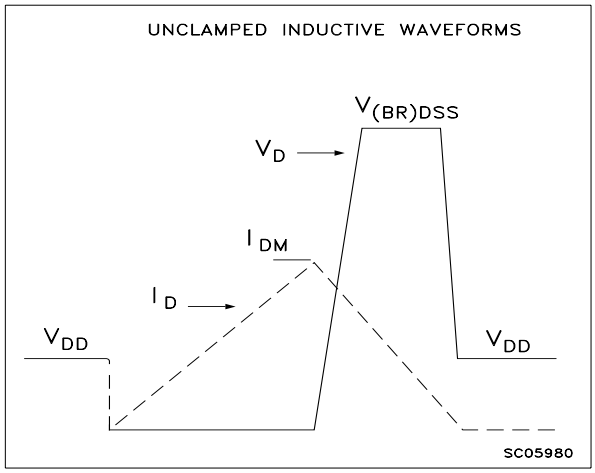


Fig. 3: Switching Times Test Circuit For Resistive Load

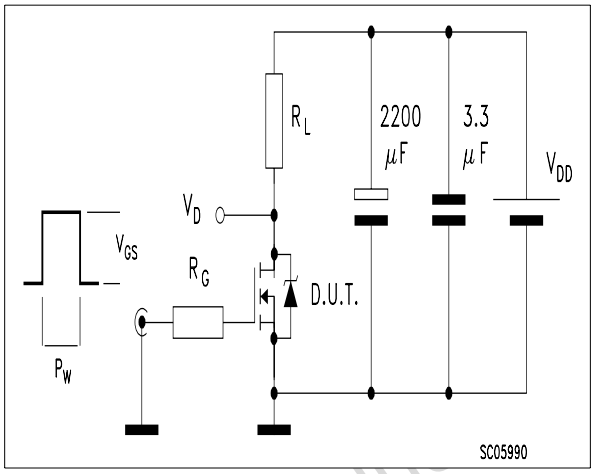


Fig. 4: Gate Charge test Circuit

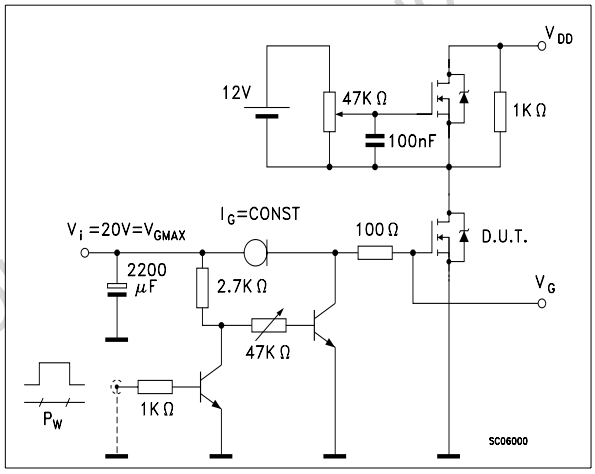
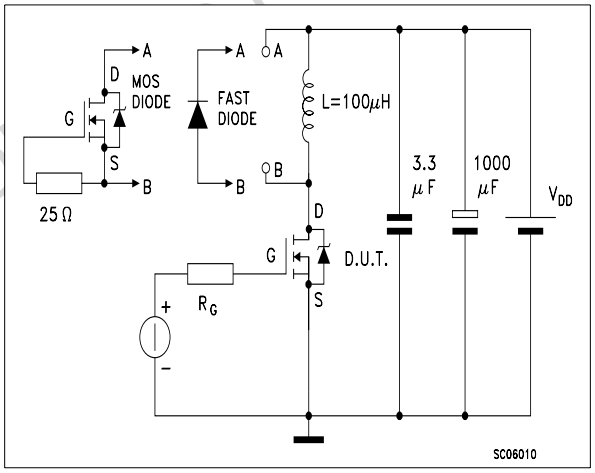
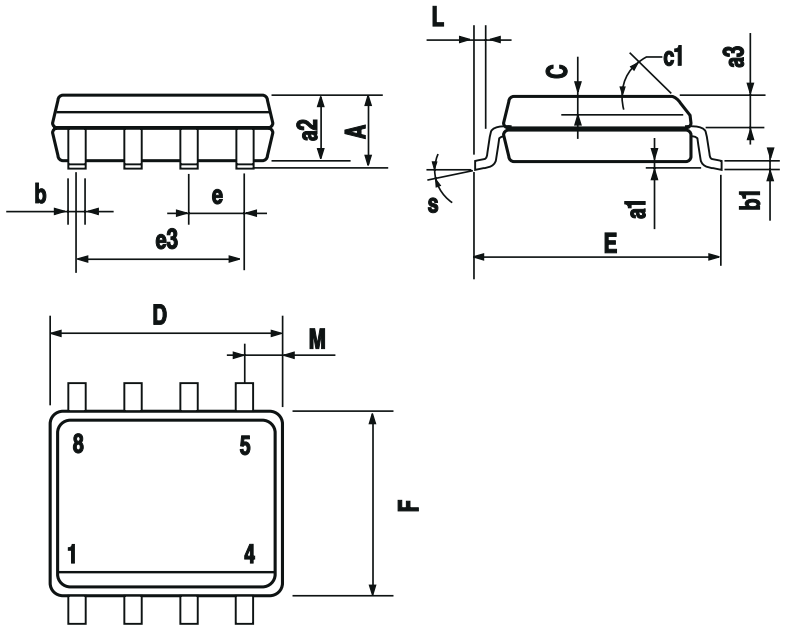


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



SO-8 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



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